/ Descriptions

TO-220 N MOS N-CHANNEL MOSFET in a TO-220 Plastic Package.

/ Features

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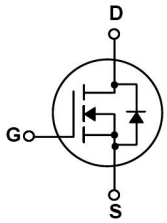
Low gate charge, low crss, fast switching.

/ Applications

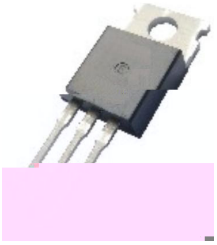
DC/DC

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

/ Equivalent Circuit



/ Pinning



PIN1 G PIN 2 D PIN 3 S

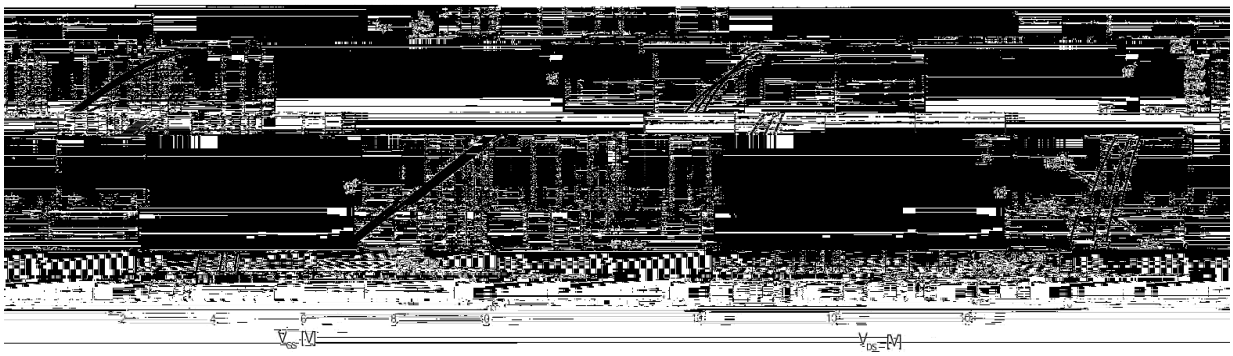
/ h_{FE} Classifications & Marking

See Marking Instructions.

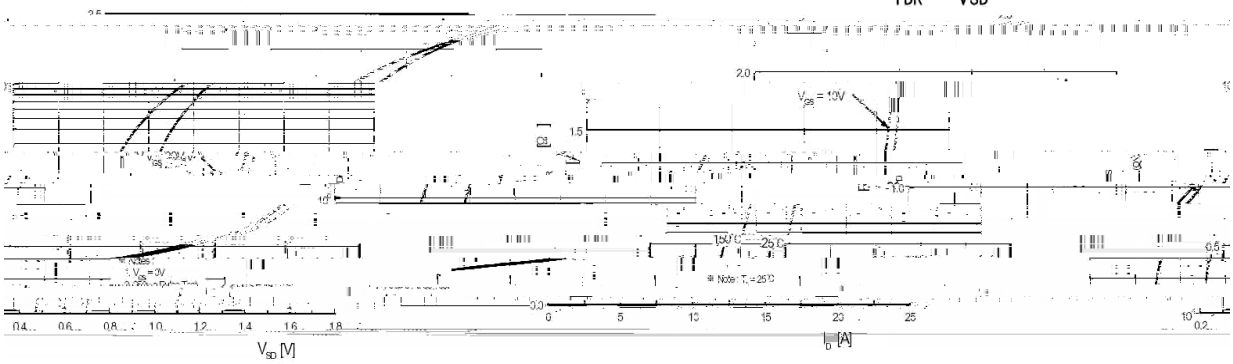
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	200	V
Drain Current	I_D(Tc=25)	9.0	A
	I_D(Tc=100)	5.7	A
Pulsed Drain Current	I_{DM}	36	A
Gate-Source Voltage	V_{GSS}	±30	V
Avalanche Current	I_{AR}	9.0	A
Single Pulsed Avalanche Energy	E_{AS}	162	mJ
Repetitive Avalanche Energy	E_{AR}	7.8	mJ
Total Power Dissipation	P_D(Tc=25)	72	W
Junction and Storage Temperature Range	T_J,T		

/ Electrical Characteristic Curve

ID – VDS

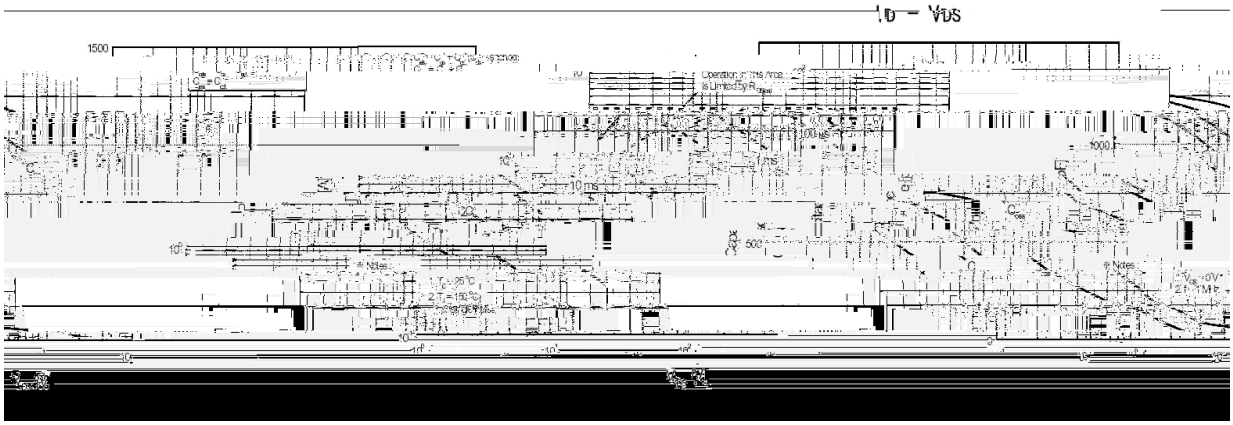


RDS(ON) – ID

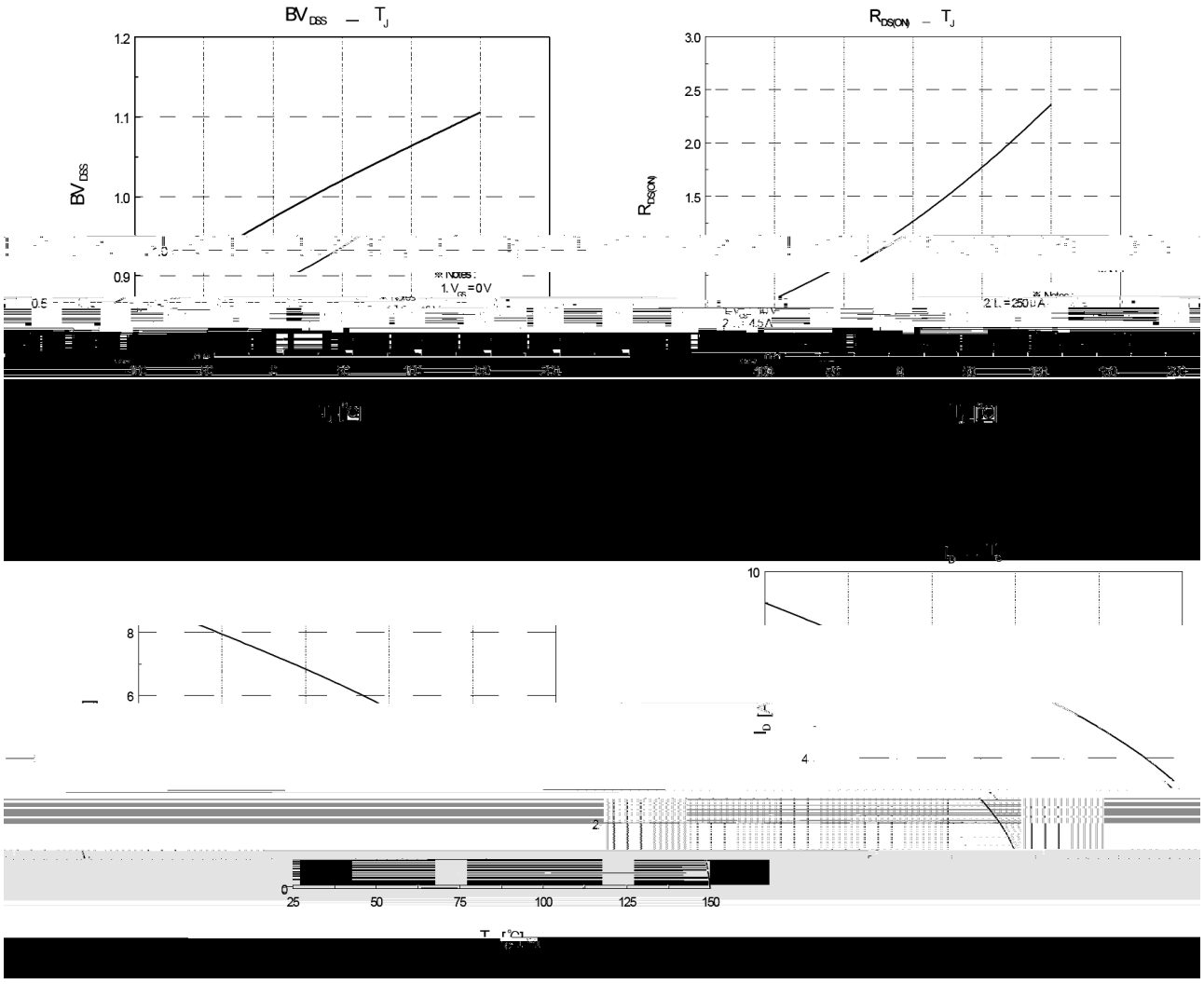


IDR – VSD

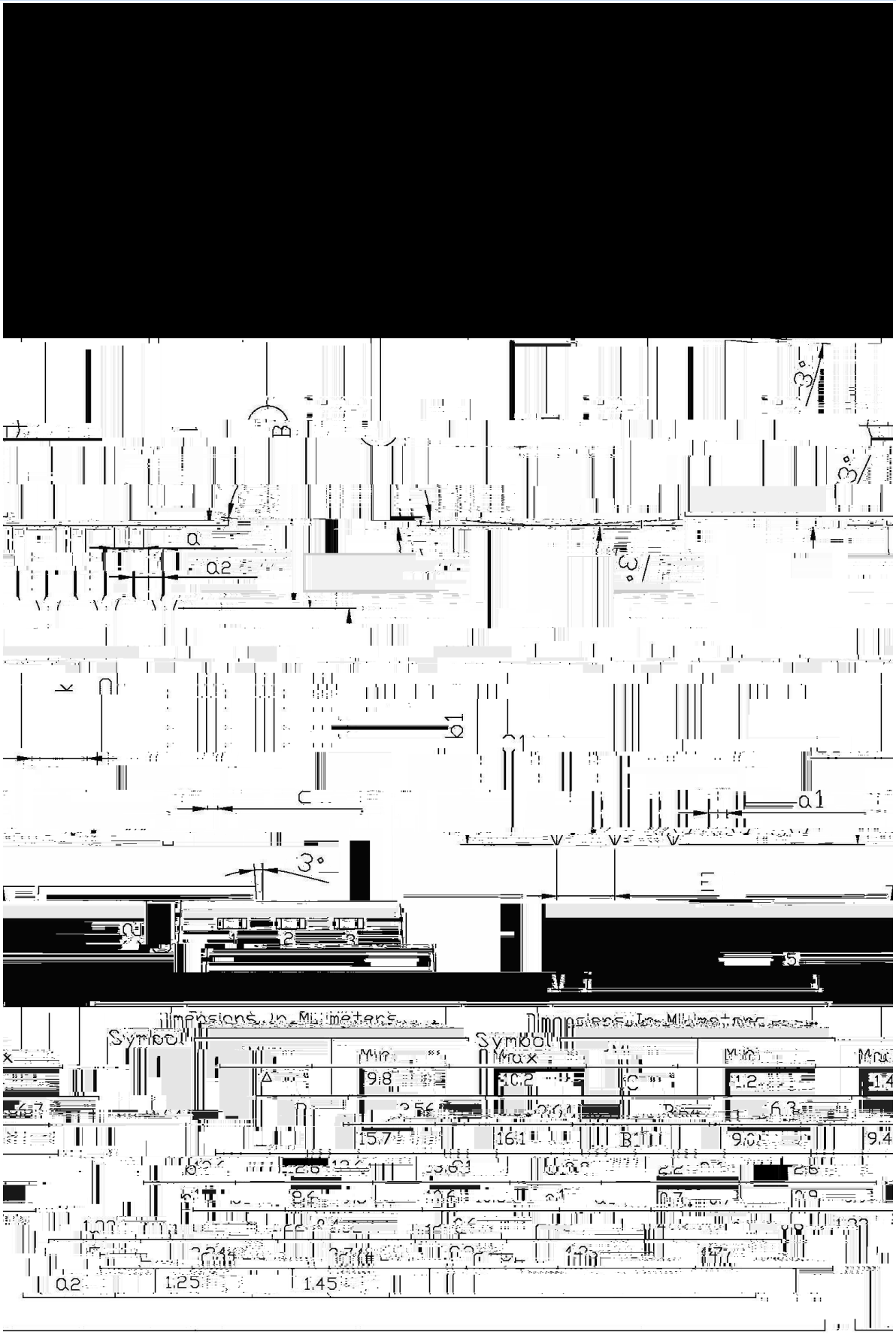
ID – VDS



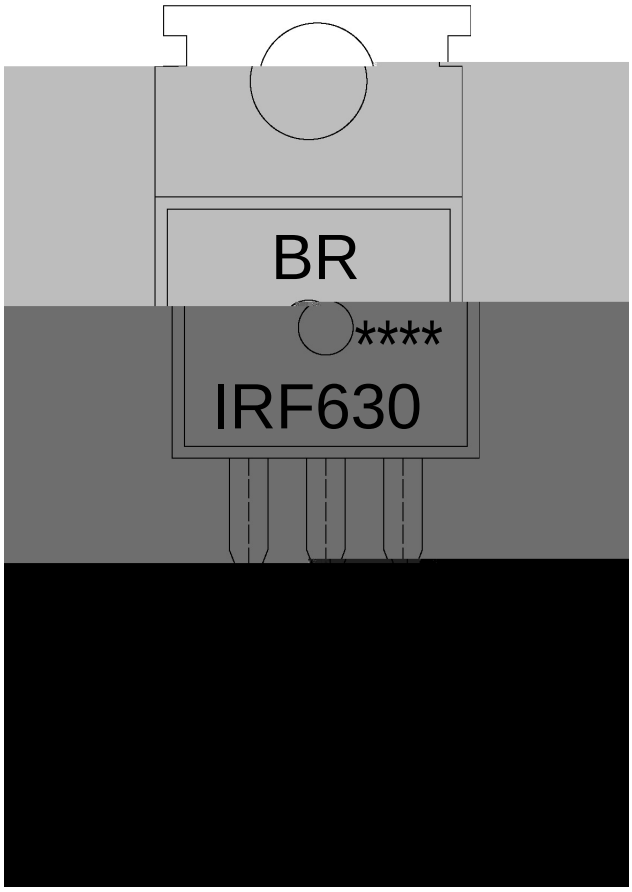
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



BR

IRF630

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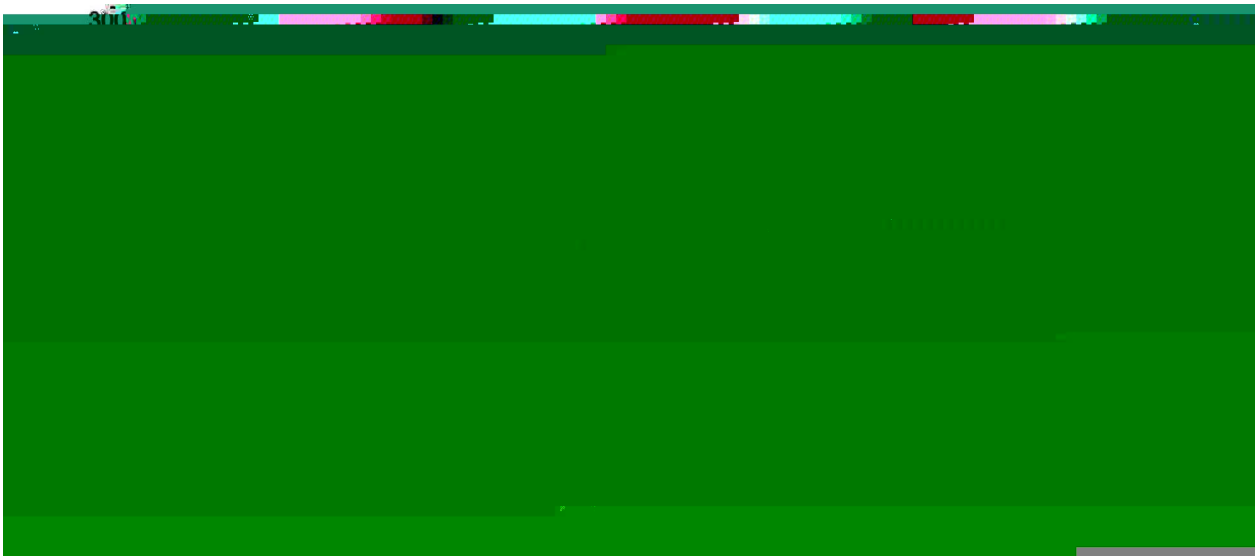
Note:

BR:	Company Code
IRF630:	Product Type.
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



			Note:
1	25 150	60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2	255±5	5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.
3	2 10 /sec.		3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270±5	10±1 sec.	Temp.:270±5	Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units					Dimension		(unit mm³)
	Units/Bag /	Bags/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Bag	Inner Box	Outer Box
TO-220/F	200	10	2,000	5	10,000	135×190	237×172×102	560×245×195

/ TUBE

Package Type	Units					Dimension		(unit mm³)
	Units/Tube /	Tubes/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Tube	Inner Box	Outer Box
TO-220/F	50	20	1,000	5	5,000	532×31.4×5.5	555×164×50	575×290×180

/ Notices